

C3D1P7060Q

Silicon Carbide Schottky Diode

Z-REC™ RECTIFIER

V_{RRM}	600 V
$I_F, T_C < 150^\circ\text{C}$	1.7 A
Q_C	5.6 nC

Features

- 600-Volt Schottky Rectifier
- Optimized for PFC Boost Diode Application
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on V_F

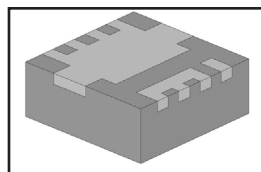
Benefits

- Small compact surface mount package
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

Applications

- Switch Mode Power Supplies
- LED Lighting

Package



PowerQFN 3.3x3.3



Part Number	Package	Marking
C3D1P7060Q	QFN 3.3	C3D1P7060

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	600	V		
V_{RSM}	Surge Peak Reverse Voltage	600	V		
V_{DC}	DC Blocking Voltage	600	V		
I_F	Continuous Forward Current	1.7 3	A A	$T_C < 150^\circ\text{C}$, No AC Component $T_C < 135^\circ\text{C}$, No AC Component	See Fig 3
I_{FRM}	Repetitive Peak Forward Surge Current	7 4.4	A	$T_C = 25^\circ\text{C}$, $t_p = 10$ ms, Half Sine pulse $T_C = 110^\circ\text{C}$, $t_p = 10$ ms, Half Sine pulse	
I_{FSM}	Non-Repetitive Peak Forward Surge Current	15 12	A	$T_C = 25^\circ\text{C}$, $t_p = 10$ ms, Half Sine pulse $T_C = 110^\circ\text{C}$, $t_p = 10$ ms, Half Sine pulse	
P_{tot}	Power Dissipation	35.5 13	W	$T_C = 25^\circ\text{C}$ $T_C = 110^\circ\text{C}$	
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +160	$^\circ\text{C}$		
T_C	Maximum Case Temperature	150	$^\circ\text{C}$		

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.5 1.8	1.7 2.4	V	$I_F = 1.7 \text{ A}$ $T_C = 25^\circ\text{C}$ $I_F = 1.7 \text{ A}$ $T_C = 150^\circ\text{C}$	
I_R	Reverse Current	10 20	50 100	μA	$V_R = 600 \text{ V}$ $T_C = 25^\circ\text{C}$ $V_R = 600 \text{ V}$ $T_C = 150^\circ\text{C}$	
Q_C	Total Capacitive Charge	5.6		nC	$V_R = 600 \text{ V}$, $I_F = 1.7 \text{ A}$ $dI/dt = 500 \text{ A}/\mu\text{s}$ $T_C = 25^\circ\text{C}$	
C	Total Capacitance	100 7 6		pF	$V_R = 0 \text{ V}$, $T_C = 25^\circ\text{C}$, $f = 1 \text{ MHz}$ $V_R = 200 \text{ V}$, $T_C = 25^\circ\text{C}$, $f = 1 \text{ MHz}$ $V_R = 400 \text{ V}$, $T_C = 25^\circ\text{C}$, $f = 1 \text{ MHz}$	

Note:

1. This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Symbol	Parameter	Typ.	Unit
$R_{\theta JC}$	Package Thermal Resistance from Junction to Case	3.8	$^\circ\text{C}/\text{W}$

Typical Performance

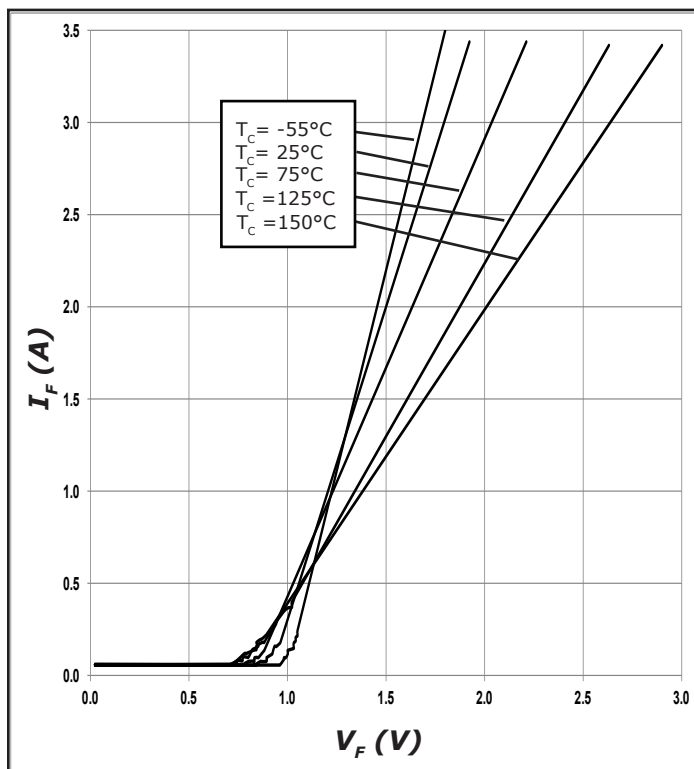


Figure 1. Forward Characteristics

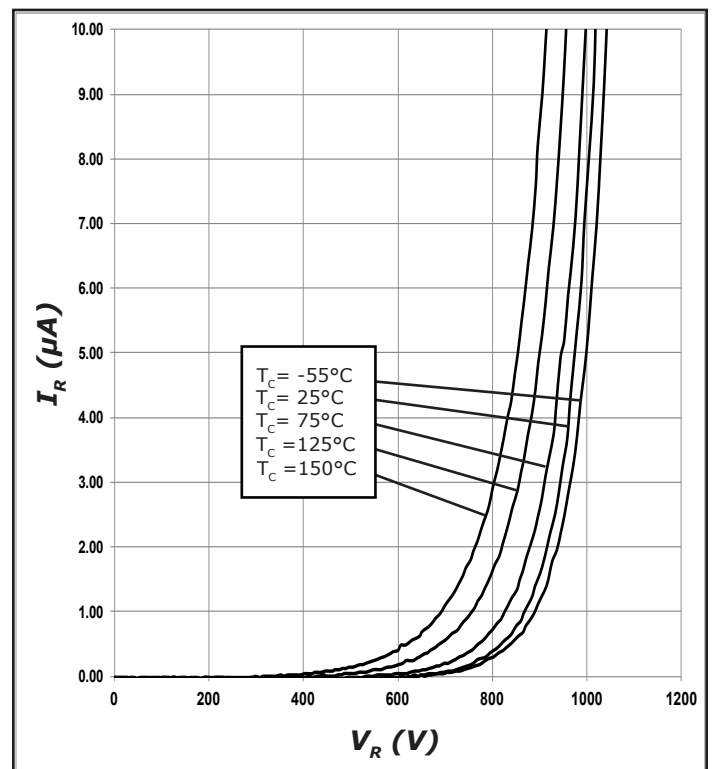


Figure 2. Reverse Characteristics

Typical Performance

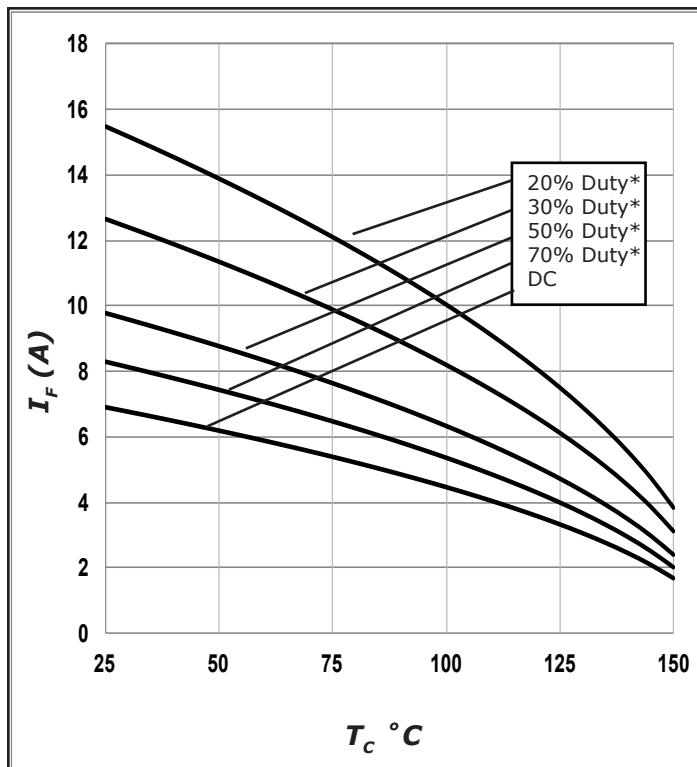


Figure 3. Current Derating

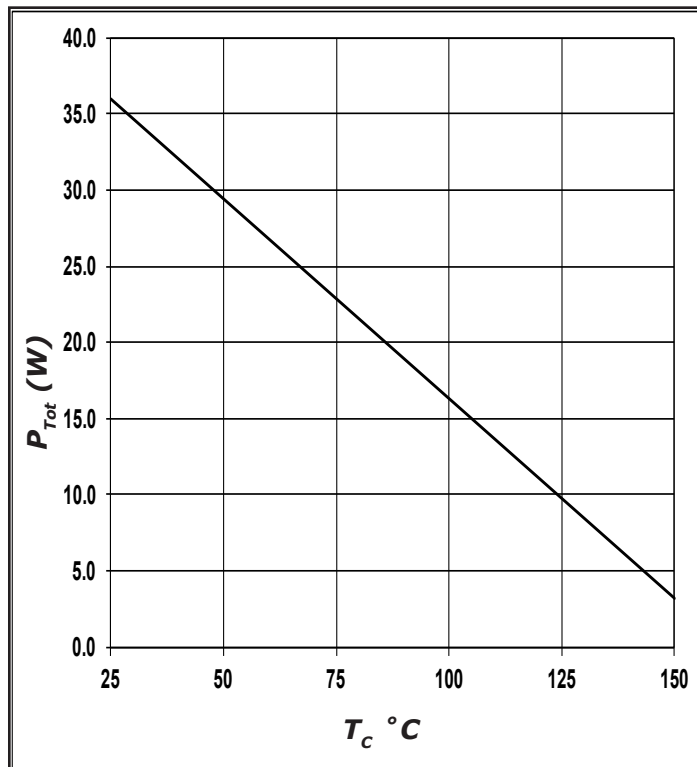


Figure 4. Power Derating

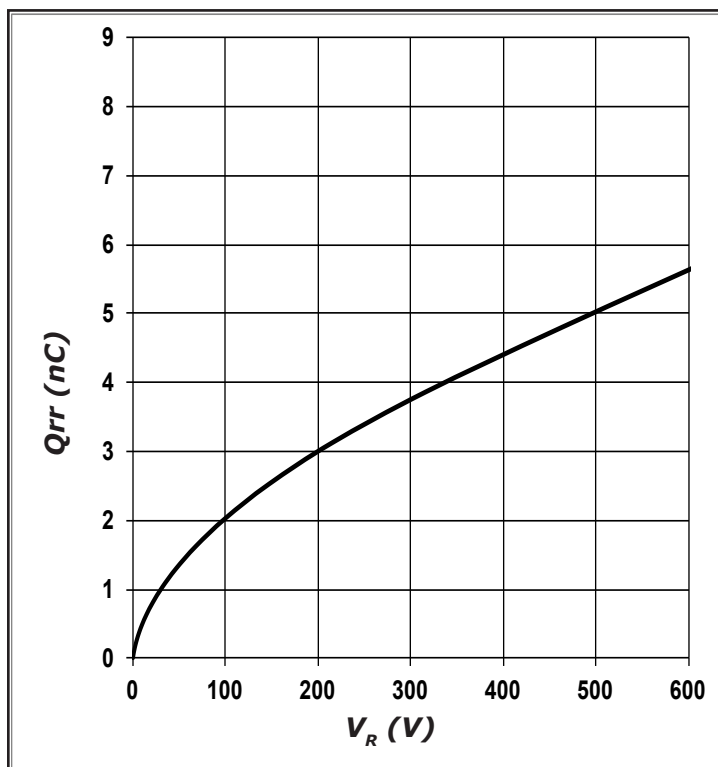


Figure 5. Recovery Charge vs. Reverse Voltage

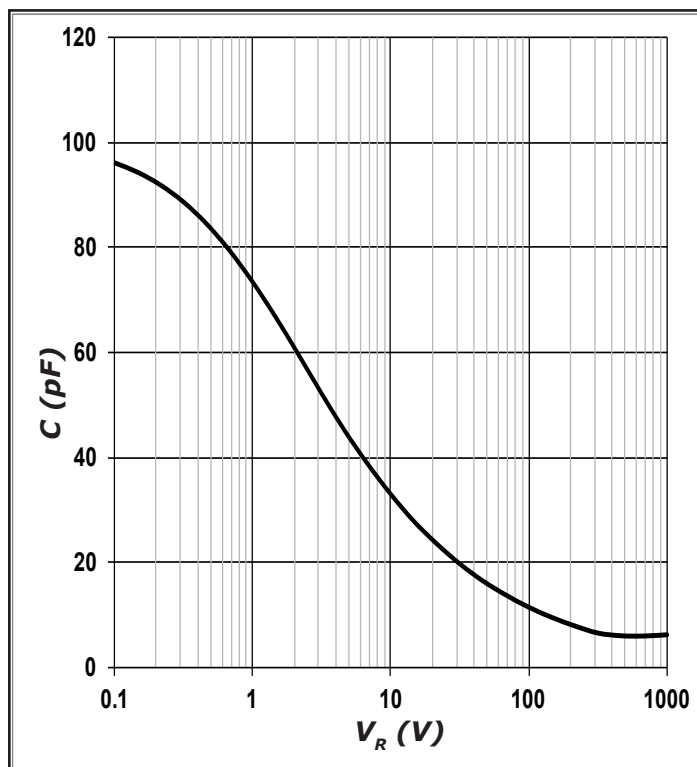


Figure 6. Capacitance vs. Reverse Voltage

Typical Performance

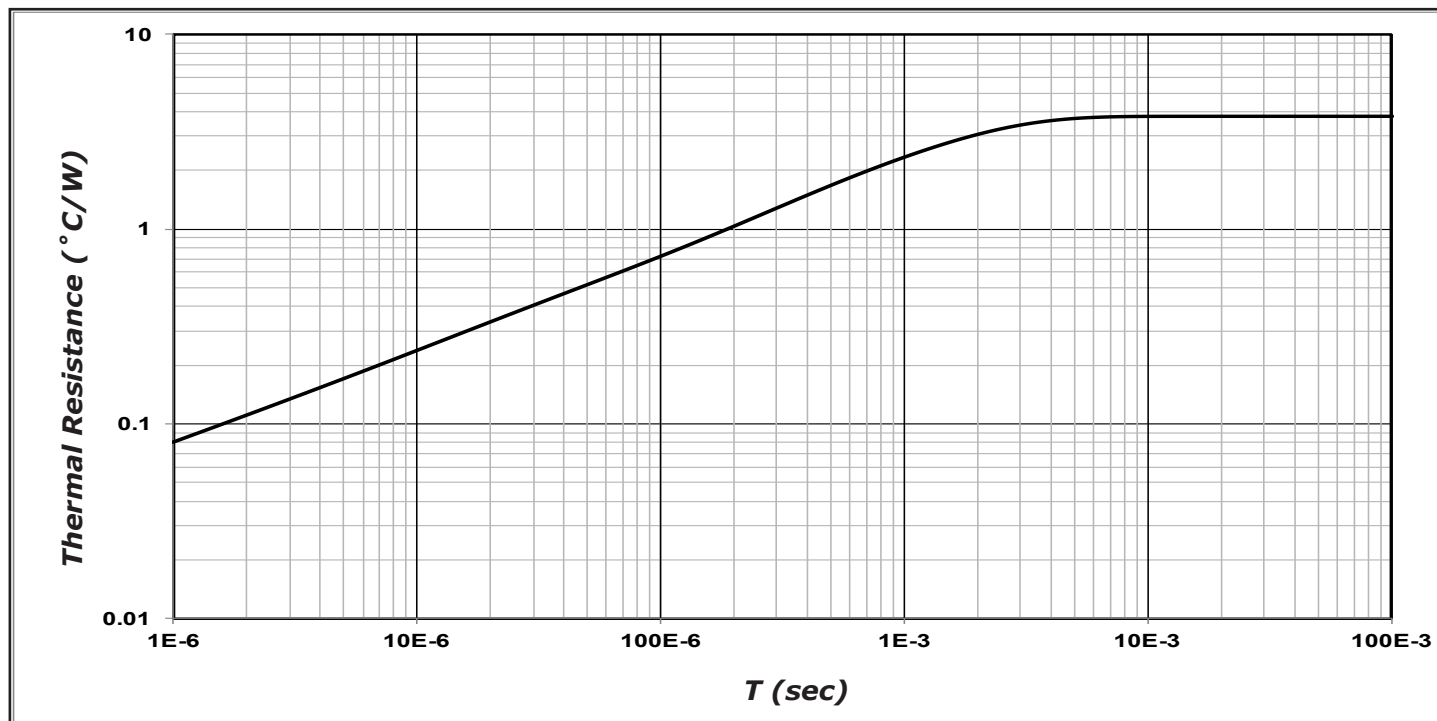
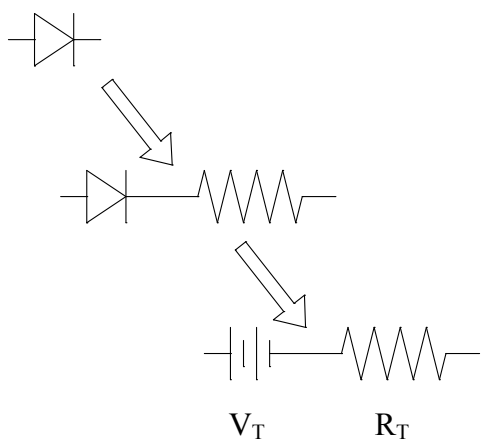


Figure 7. Transient Thermal Impedance

Diode Model



$$V_{f_T} = V_T + I_f \cdot R_T$$

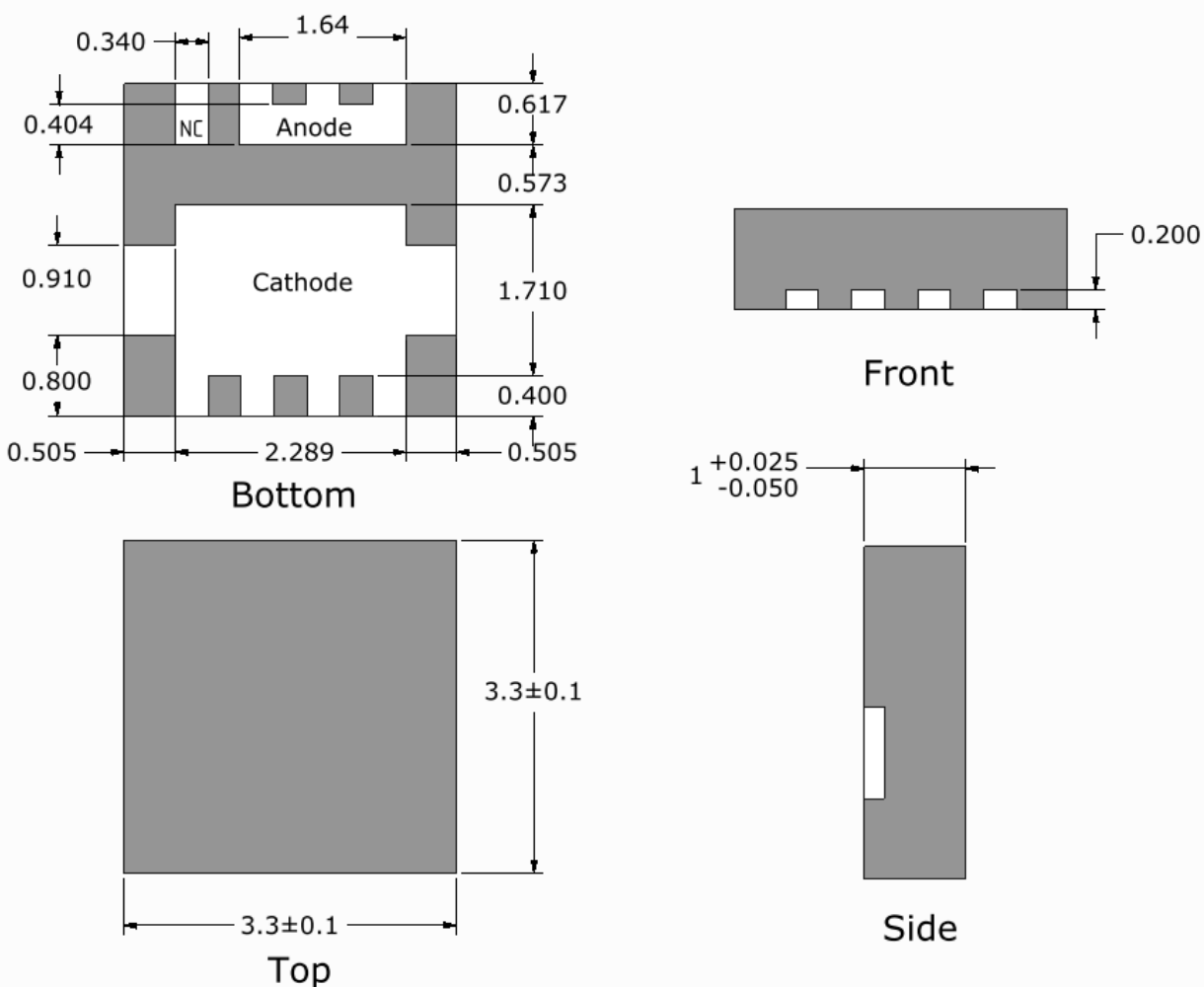
$$V_T = 0.99 + (T_j \cdot -1.5 \cdot 10^{-3})$$

$$R_T = 0.22 + (T_j \cdot 2.6 \cdot 10^{-3})$$

Note: T_j = Diode Junction Temperature In Degrees Celsius

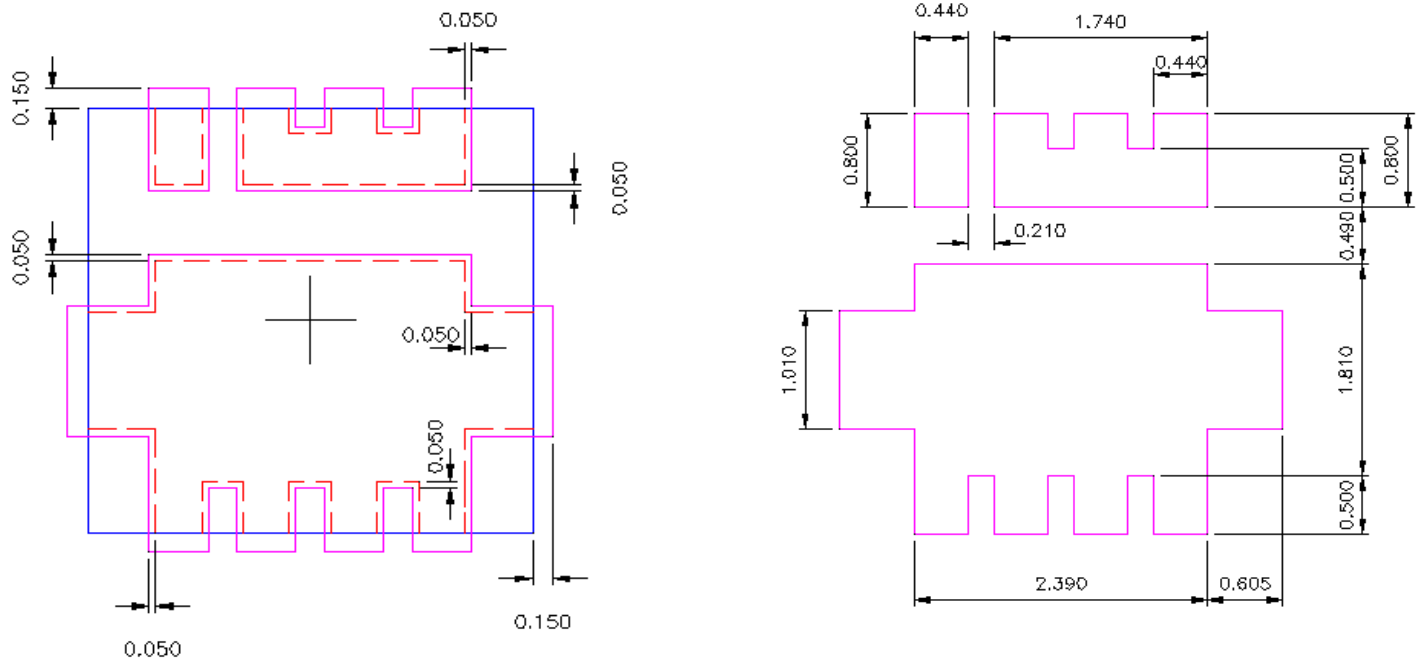
Package Dimensions

Package QFN 3.3



All Dimensions are in mm
Tolerances are 0.05 mm if not specified
NC = No Connect

Recommended Landing Pattern (All Dimensions are in mm)



Note: The design of the land pattern and the size of the thermal pad depend mainly on the thermal characteristic and power dissipation. In general, the size of the thermal pad should be as close to the exposed pad of the package as possible, provided that there is no bridging between the thermal pad and the lead pads.

The 0.050mm extra length and width provides space to accommodate the placement tolerance of the component during pick and place process. The 0.150mm along the perimeter present areas for solder to form fillet along the side metal edges of the package.

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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